TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

2SC3011

UHF~C Band Low Noise Amplifier Applications

Unit: mm

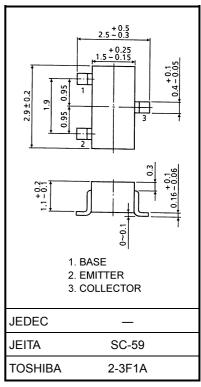
• High gain: $|S_{21e}|^2 = 12dB$ (typ.)

• Low noise figure: NF = 2.3dB (typ.), f = 1 GHz

• High f_T : $f_T = 6.5 \text{ GHz}$

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	20	V
Collector-emitter voltage	V _{CEO}	7	V
Emitter-base voltage	V _{EBO}	3	V
Collector current	Ic	30	mA
Emitter current	lΕ	10	mA
Collector power dissipation	PC	150	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C



Weight: 0.012 g (typ.)

Microwave Characteristics (Ta = 25°C)

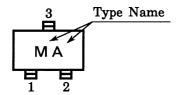
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Transition frequency	f _T	$V_{CE} = 5 \text{ V}, I_{C} = 10 \text{ mA}$	_	6.5	_	GHz
Insertion gain	S _{21e} ²	$V_{CE} = 5 \text{ V}, I_{C} = 10 \text{ mA}, f = 1 \text{ GHz}$	_	12	_	dB
Noise figure	NF	$V_{CE} = 5 \text{ V}, I_{C} = 5 \text{ mA}, f = 1 \text{ GHz}$	_	2.3	_	dB

Electrical Characteristics (Ta = 25°C)

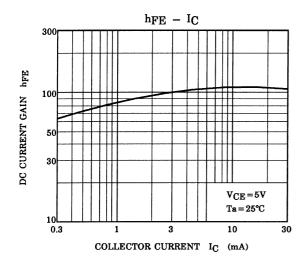
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 10 V, I _E = 0	_	_	1.0	μА
Emitter cut-off current	I _{EBO}	V _{EB} = 1.0 V, I _C = 0	_	_	1.0	μА
Collecter-emitter breakdown voltage	V (BR) CEO	$I_C = 0.5 \text{ mA}, I_B = 0$	7	_	_	V
DC current gain	h _{FE}	V _{CE} = 5 V, I _C = 10 mA	30	120	_	
Collector-emitter saturation voltage	V _{CE} (sat)	I _C = 10 mA, I _B = 1 mA	_	0.1	_	V
Base-emitter saturation voltage	V _{BE (sat)}		_	0.87	_	V
Collecter output capacitance	C _{ob}	$V_{CB} = 5 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$ (Note)	_	0.7	0.9	pF
Reverse transfer capacitance	C _{re}		_	0.5	_	pF
Input capacitance	C _{ib}	V _{EB} = 0, I _C = 0, f = 1 MHz	_	0.8	_	pF

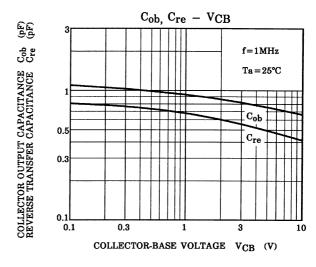
Note: C_{re} is measured by 3-terminal method with capacitance bridge.

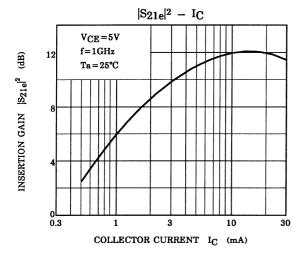
Marking

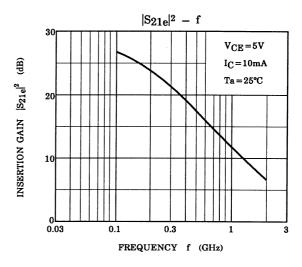


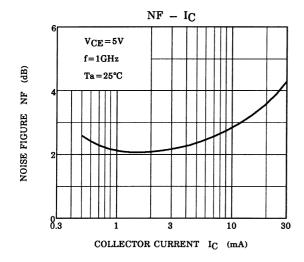
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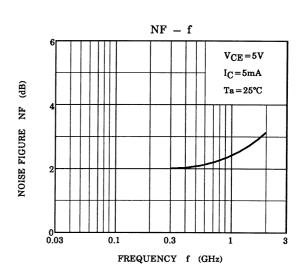






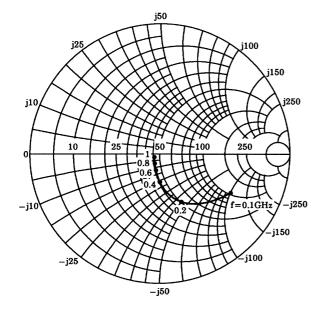


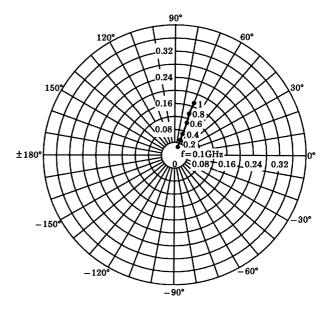




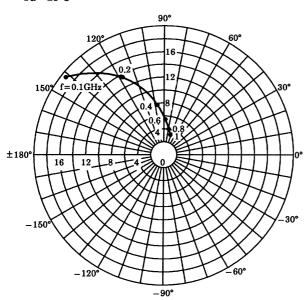
 S_{11e} $V_{CE}=5V$ $I_{C}=10mA$ $T_{a}=25^{\circ}C$ $(UNIT: \Omega)$







 S_{21e} $V_{CE}=5V$ $I_{C}=10$ mA $T_{a}=25$ °C



S_{22e} VCE=5V $I_C = 10 \text{mA}$ $T_a = 25 ^{\circ}C$ (UNIT: Ω) j50 j25 j100 j150 j10 j250 10 100 250 f=0.1GHz -j250 -j150 -j100

4

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